MC14012B

Dual 4-Input NAND Gates

The MC14012B dual 4−input NAND gates are constructed with P−Channel and N−Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low−Power TTL Loads or One Low−Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin−for−Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- This Device is Pb−Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 1)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: “D/DW” Package: –7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

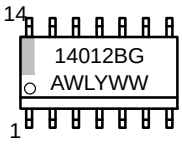
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

ON Semiconductor®

http://onsemi.com

SOIC−14
D SUFFIX
CASE 751A

MARKING DIAGRAM

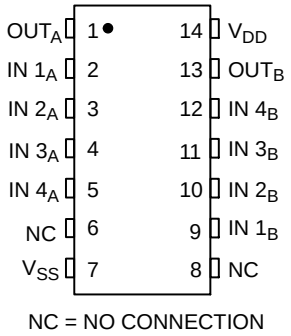


A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb−Free Package

ORDERING INFORMATION

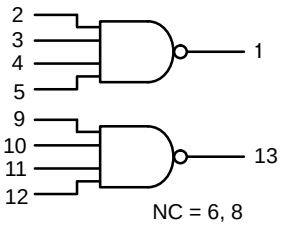
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MC14012B
Dual 4−Input NAND Gate



NC = NO CONNECTION

Figure 1. Pin Assignment



V_{DD} = PIN 14
V_{SS} = PIN 7

Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping†
MC14012BDG	SOIC−14 (Pb−Free)	55 Units / Rail
NLV14012BDG*	SOIC−14 (Pb−Free)	55 Units / Rail
MC14012BDR2G	SOIC−14 (Pb−Free)	2500 Units / Tape & Reel
NLV14012BDR2G*	SOIC−14 (Pb−Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	−55°C Min	−55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level	V_{OL}	5.0	−	0.05	−	0	0.05	−	0.05	Vdc
V_{in} = V_{DD} or 0		10	−	0.05	−	0	0.05	−	0.05	
		15	−	0.05	−	0	0.05	−	0.05	
“1” Level	V_{OH}	5.0	4.95	−	4.95	5.0	−	4.95	−	Vdc
V_{in} = 0 or V_{DD}		10	9.95	−	9.95	10	−	9.95	−	
		15	14.95	−	14.95	15	−	14.95	−	
Input Voltage “0” Level	V_{IL}									Vdc
(V_O = 4.5 or 0.5 Vdc)		5.0	−	1.5	−	2.25	1.5	−	1.5	
(V_O = 9.0 or 1.0 Vdc)		10	−	3.0	−	4.50	3.0	−	3.0	
(V_O = 13.5 or 1.5 Vdc)		15	−	4.0	−	6.75	4.0	−	4.0	
“1” Level	V_{IH}									Vdc
(V_O = 0.5 or 4.5 Vdc)		5.0	3.5	−	3.5	2.75	−	3.5	−	
(V_O = 1.0 or 9.0 Vdc)		10	7.0	−	7.0	5.50	−	7.0	−	
(V_O = 1.5 or 13.5 Vdc)		15	11	−	11	8.25	−	11	−	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	–3.0	−	–2.4	–4.2	−	–1.7	−	
(V_{OH} = 4.6 Vdc)		5.0	–0.64	−	–0.51	–0.88	−	–0.36	−	
(V_{OH} = 9.5 Vdc)		10	–1.6	−	–1.3	–2.25	−	–0.9	−	
(V_{OH} = 13.5 Vdc)		15	–4.2	−	–3.4	–8.8	−	–2.4	−	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	−	0.51	0.88	−	0.36	−	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	−	1.3	2.25	−	0.9	−	
(V_{OL} = 1.5 Vdc)		15	4.2	−	3.4	8.8	−	2.4	−	
Input Current	I_{in}	15	−	±0.1	−	±0.00001	±0.1	−	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	−	−	−	−	5.0	7.5	−	−	pF
Quiescent Current (Per Package)	I_{DD}	5.0	−	0.25	−	0.0005	0.25	−	7.5	μAdc
		10	−	0.5	−	0.0010	0.5	−	15	
		15	−	1.0	−	0.0015	1.0	−	30	
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Gate, C_L = 50 pF)	I_T	5.0	I_T = (0.3 μA/kHz) f + I_{DD}/N							μAdc
		10	I_T = (0.6 μA/kHz) f + I_{DD}/N							
		15	I_T = (0.9 μA/kHz) f + I_{DD}/N							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

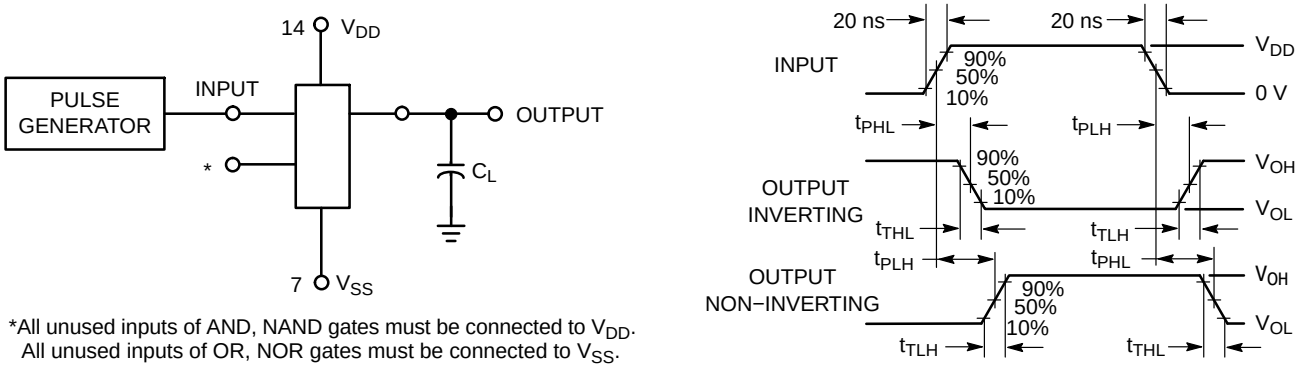
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} − V_{SS}) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (1.35 ns/pF) C_L + 33 ns		5.0	–	100	200	
t_{TLH} = (0.60 ns/pF) C_L + 20 ns		10	–	50	100	
t_{TLH} = (0.40 ns/PF) C_L + 20 ns		15	–	40	80	
Output Fall Time	t_{THL}					ns
t_{THL} = (1.35 ns/pF) C_L + 33 ns		5.0	–	100	200	
t_{THL} = (0.60 ns/pF) C_L + 20 ns		10	–	50	100	
t_{THL} = (0.40 ns/pF) C_L + 20 ns		15	–	40	80	
Propagation Delay Time	t_{PLH}, t_{PHL}					ns
t_{PLH}, t_{PHL} = (0.90 ns/pF) C_L + 115 ns		5.0	–	160	300	
t_{PLH}, t_{PHL} = (0.36 ns/pF) C_L + 47 ns		10	–	65	130	
t_{PLH}, t_{PHL} = (0.26 ns/pF) C_L + 37 ns		15	–	50	100	

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.



*All unused inputs of AND, NAND gates must be connected to V_{DD}.
All unused inputs of OR, NOR gates must be connected to V_{SS}.

Figure 3. Switching Time Test Circuit and Waveforms

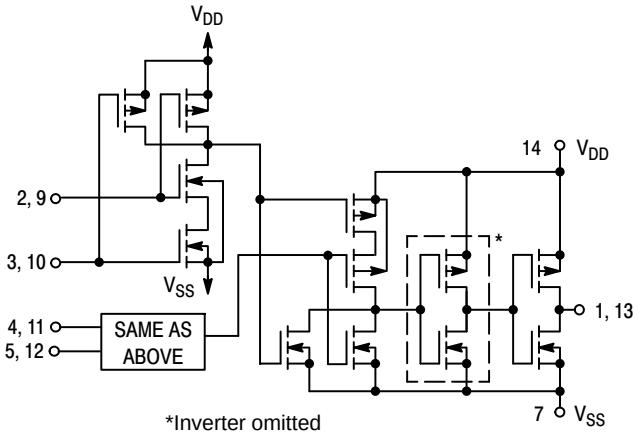


Figure 4. Circuit Schematic − One of Two Gates Shown

TYPICAL B−SERIES GATE CHARACTERISTICS

N−CHANNEL DRAIN CURRENT (SINK)

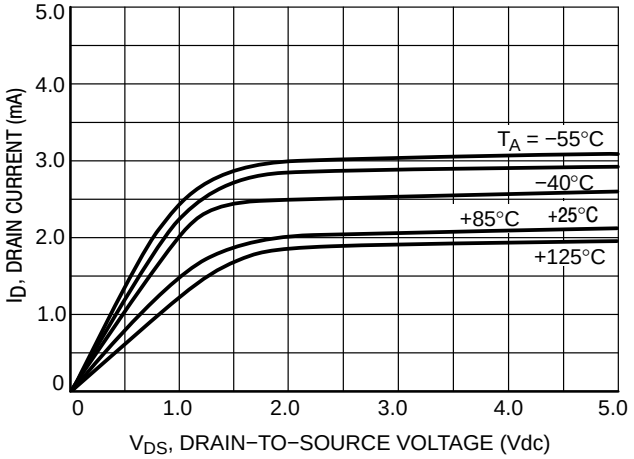


Figure 5. V_{GS} = 5.0 Vdc

P−CHANNEL DRAIN CURRENT (SOURCE)

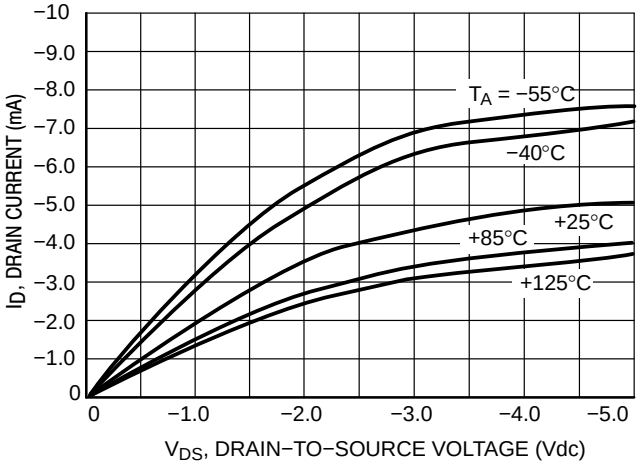


Figure 6. V_{GS} = − 5.0 Vdc

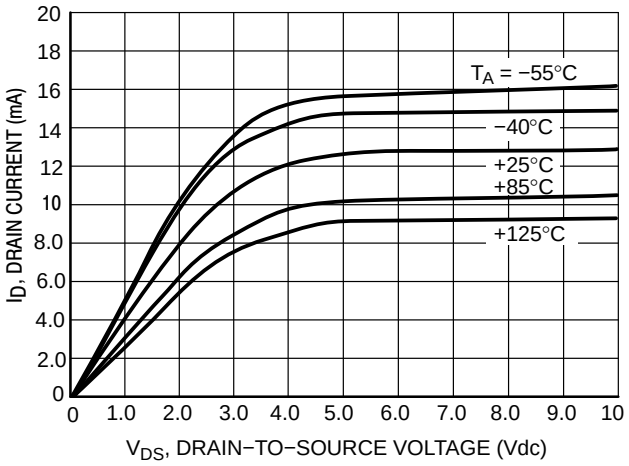


Figure 7. V_{GS} = 10 Vdc

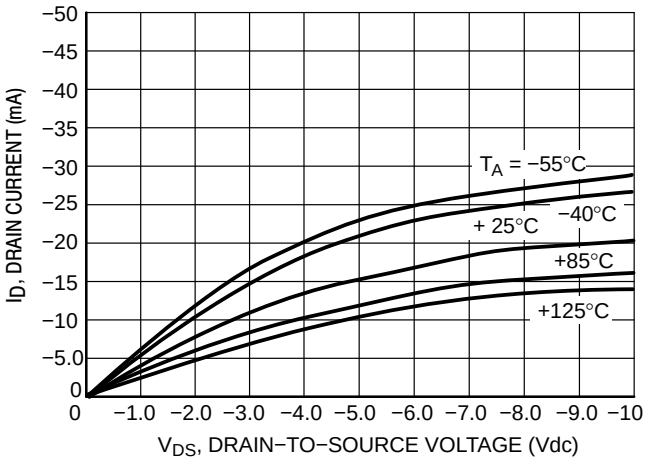


Figure 8. V_{GS} = − 10 Vdc

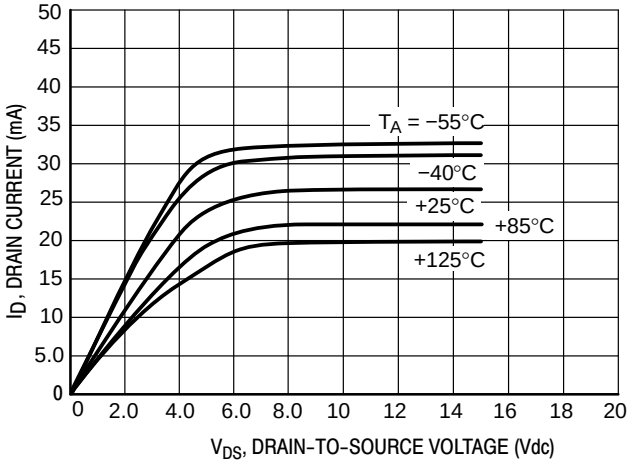


Figure 9. V_{GS} = 15 Vdc

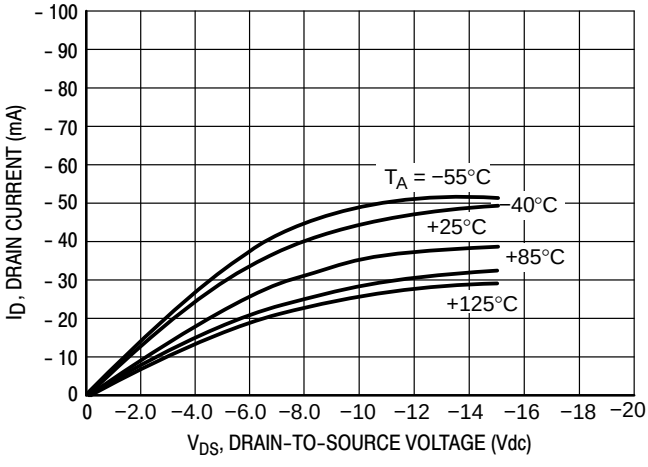


Figure 10. V_{GS} = − 15 Vdc

These typical curves are not guarantees, but are design aids.
Caution: The maximum rating for output current is 10 mA per pin.

VOLTAGE TRANSFER CHARACTERISTICS

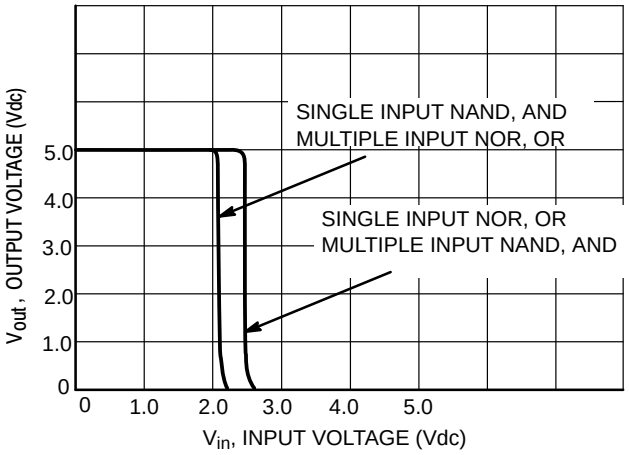


Figure 11. V_{DD} = 5.0 Vdc

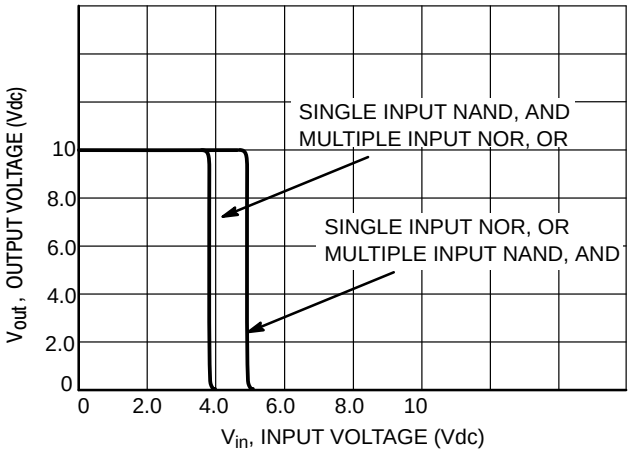


Figure 12. V_{DD} = 10 Vdc

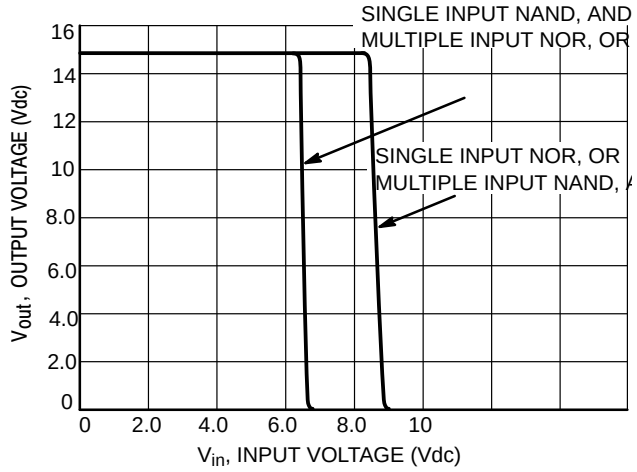


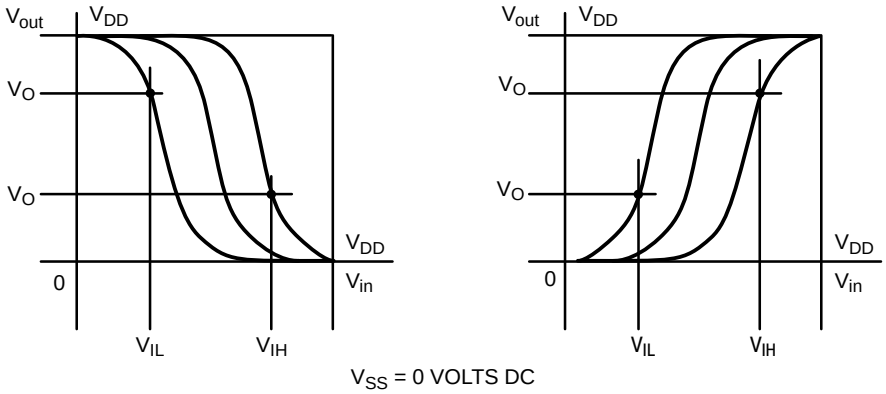
Figure 13. V_{DD} = 15 Vdc

DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal “1” or “0” input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the “1” and “0” levels =

1.0 V with a 5.0 V supply
2.0 V with a 10.0 V supply
2.5 V with a 15.0 V supply

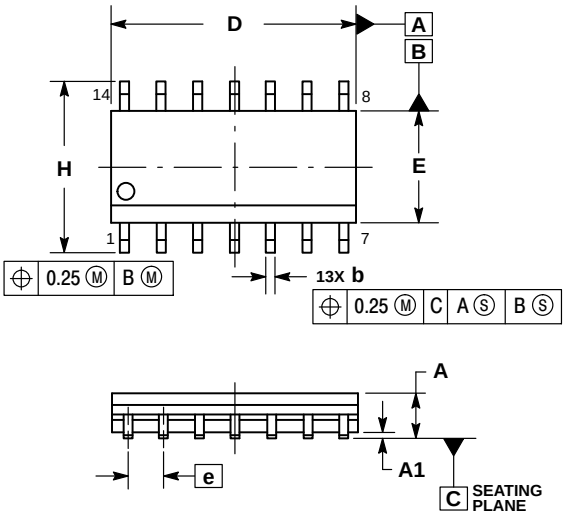


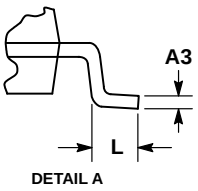
(a) Inverting Function **(b) Non−Inverting Function**

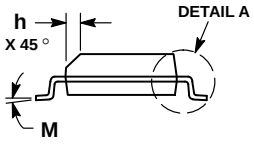
Figure 14. DC Noise Immunity

PACKAGE DIMENSIONS

SOIC−14 NB
CASE 751A−03
ISSUE K



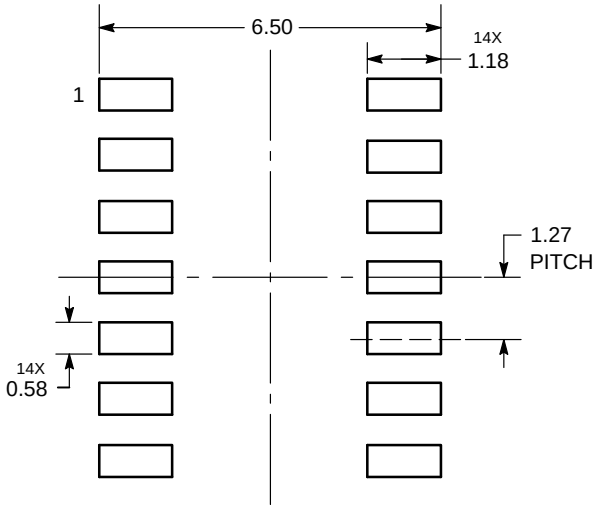




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

MC14012BDG MC14012BDR2G NLV14012BDR2G NLV14012BDG